

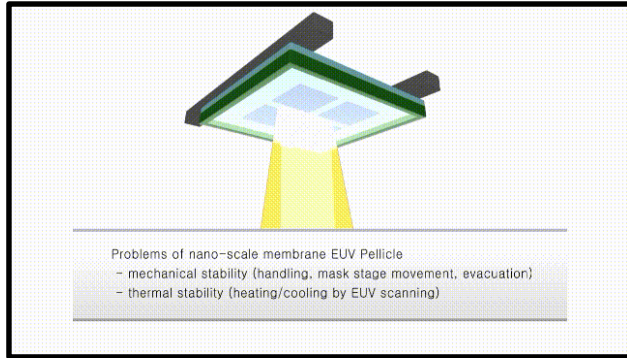


Characterization of SiN-based membrane for EUV pellicle application

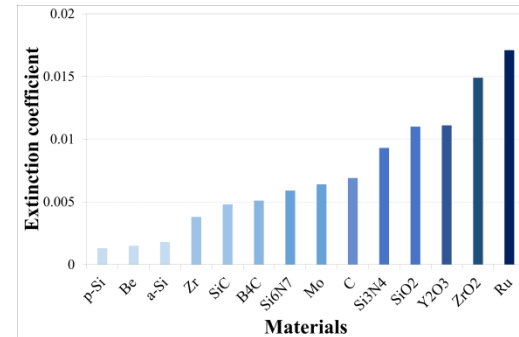
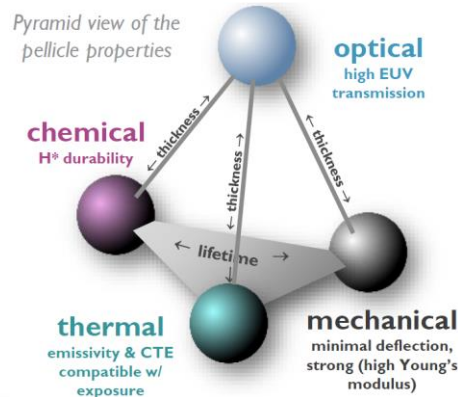
Junghwan Kim, Yongjoo Jang, Inseon Jung, Hyekeun Oh and Jinho Ahn
Hanyang University

EUV Pellicle Requirements

Pellicle is a dust cover preventing particles and contaminants from falling on the mask.

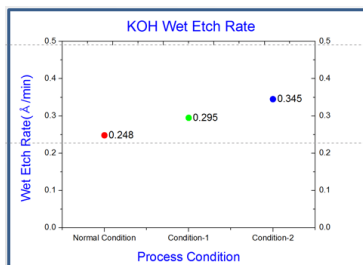
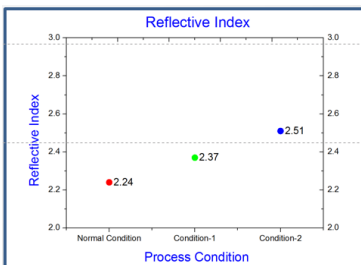
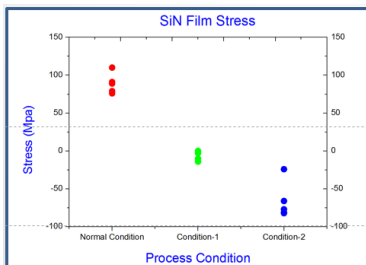
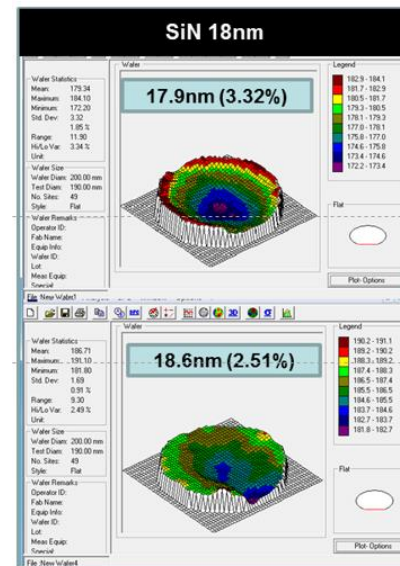
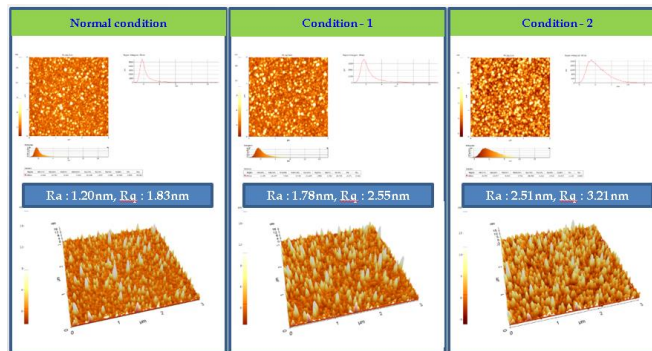
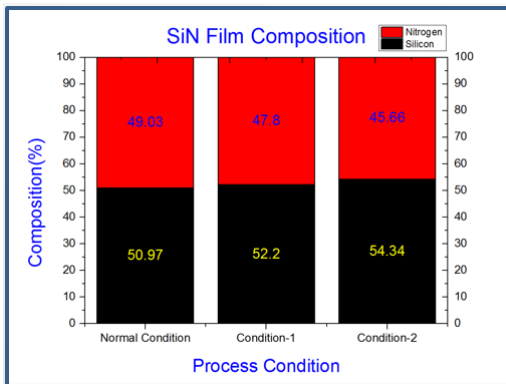


	Item	Requirement
Pellicle material requirements	Pellicle film EUV transmission	90% single pass (81% double pass)
	EUV transmission spatial non-uniformity	< 0.2% at reticle level
	EUV transmission angular non-uniformity	< 300 mrad max. local pellicle angle
	EUV intensity in scanning slit @ pellicle	5 W/cm ² (250W EUV source equivalent)
	Lifetime	~315 hrs (production hours in a EUV+H ₂ environment)
Pellicle + frame requirements	Standoff distance	2 ± 0.5 mm
	Max. acceleration	100 m/s ² during scanning
	Max. ambient pressure rate of change	< 3.5 mbar/s (peak during pump-down/ vent in the load lock)
	Reticle reserved area for pellicle assembly (centered on substrate)	110.7 mm x 144.1 mm: inner 118.0 mm x 150.7 mm: outer
Pellicle impact on imaging performance: < 0.1 nm CDU impact on wafer		



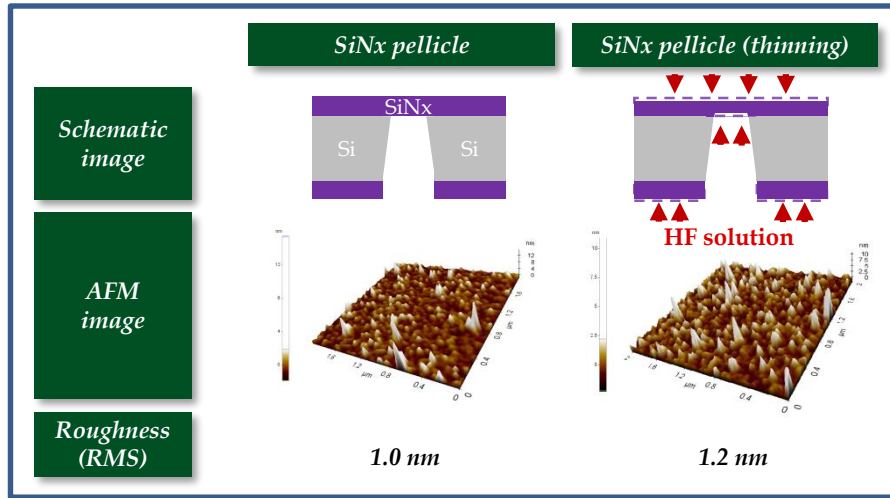
Ref. ASML, SPIE Advanced Lithography (2014) / IMEC (2017)

SiNx pellicle platform : Deposition



Atomically-smooth, uniform silicon-rich LPCVD SiNx
Stress controlled by Si:N ratio (tensile to compressive with increasing Si)

SiNx pellicle platform : Thinning Process



	Measured
43 nm SiNx	79.7 %
28 nm SiNx	85.7%
16 nm SiNx	91.1 %

SiNx can be thinned with HF solution
Surface roughness is not much degraded

A screenshot of a YouTube video player. The search bar contains 'EUV pellicle'. The video title is 'Bursting EUV pellicle high speed movie 10000fps' by HYU kim. The video thumbnail shows a dark, square-shaped object (the pellicle) that is shattering or bursting.

However, SiNx membrane shatters
when broken due to brittleness !

Strengthening Solution

Grain Boundary Strengthening

Materials with smaller grains shows higher yield strength

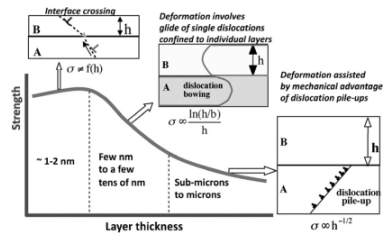


Hall-Petch Relation

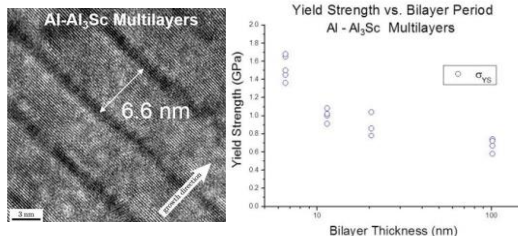
$$\sigma_{YS} = \sigma_0 + k_y \frac{1}{\sqrt{d}}$$

Nanoscale Multilayer

Multilayer is stronger than bulk material due to interface



Wang, Misra, *Curr. Opin. Sol. Sta. Mat. Sci.* 15 (2011)

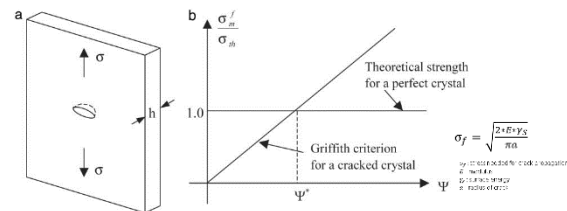


Han, Phillips, Nix, *Acta Mat.* 57 (2009)

At $h = 2-5$ nm, experimental data exhibit maximum hardness.

Brittle to Ductile Transition

Fracture strength of brittle material is always lower than theoretical strength (crack propagation: Griffith)



Crack propagation depends the sample thickness (the thinner the tougher).

$$\sigma_m^f = \alpha E_m \Psi, \quad \Psi = \sqrt{\frac{\gamma}{E_m h}}$$

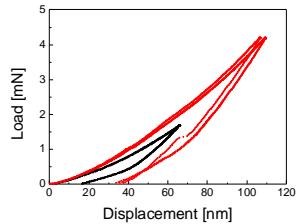
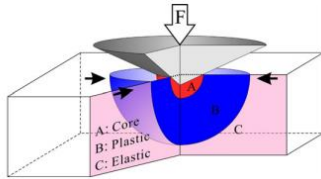
Critical thickness below which the fracture strength of cracked material is identical to that of perfect material.

$$h^* \approx \alpha^2 \frac{\gamma E_m}{\sigma_{th}^2}$$

For SiN_x case, $h^* \sim 40$ nm

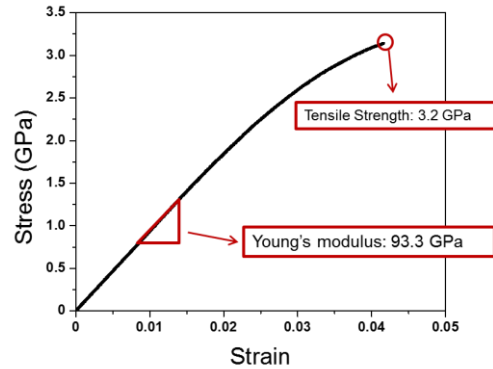
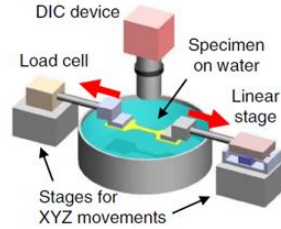
Mechanical property characterization

Nano Indentation

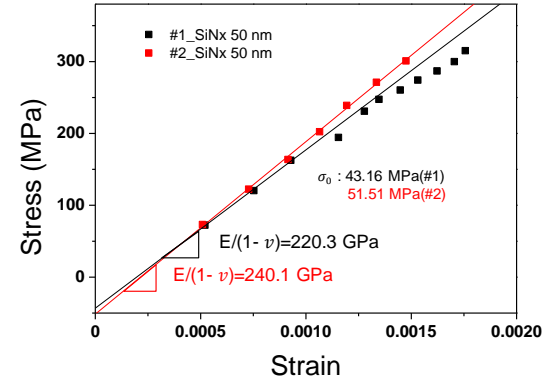
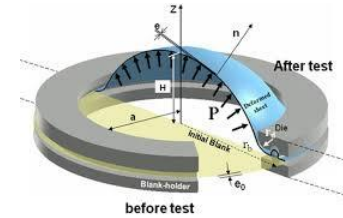


Material	Thickness	Hardness (Thin Film)
SiN _x	50nm	21.8 ± 0.42 GPa
	100nm	29.2 ± 0.05 GPa

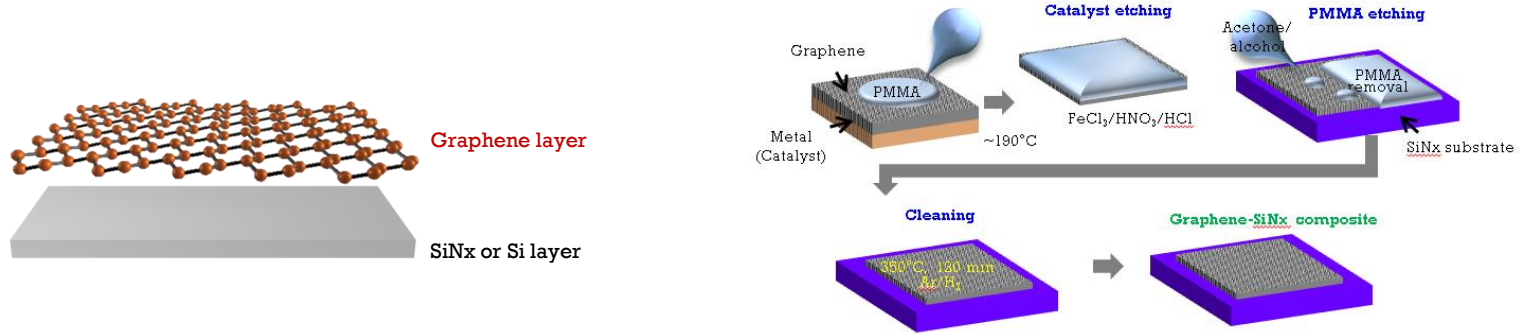
Tensile Test (in-situ SEM)



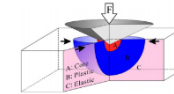
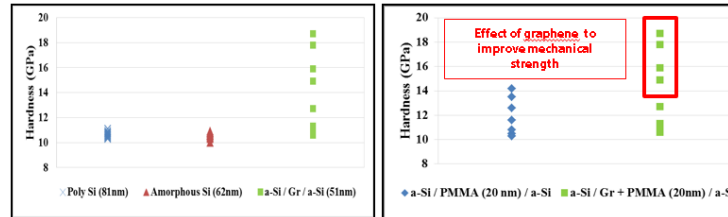
Bulge Test



Graphene Composite : Strengthening



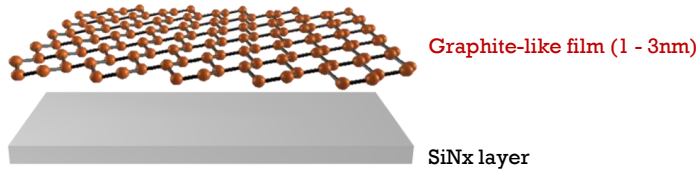
Strengthening effect by Graphene



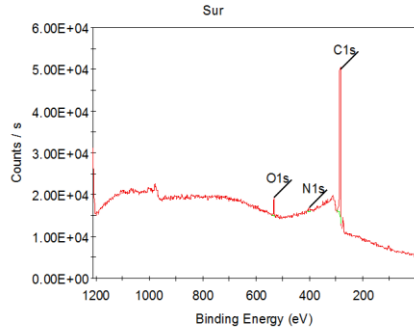
EUV absorbance of graphene ~ 0.2%/monolayer (vs. ~3% @ visible wavelength)
High possibility of composite structure with reinforcing effect of graphene
But PMMA, the material used for graphene transfer, leaves residue.

Graphite-like film using Plasma CVD

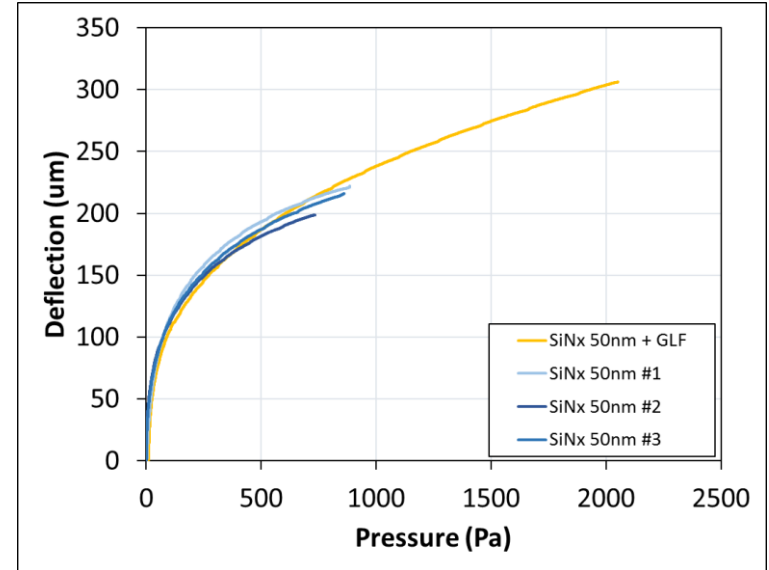
Concept



Film composition: almost carbon



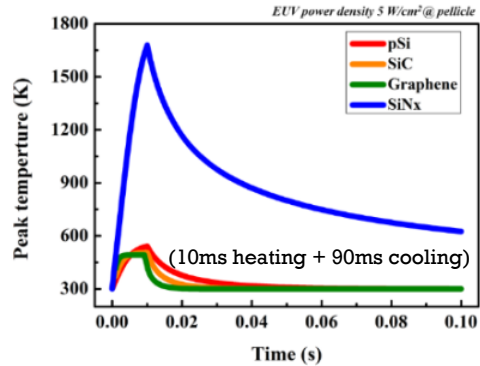
Bulge test



Nano-scale graphite film can be directly deposited on any substrate.
This composite structure shows >3X fracture strength.
Optimization will result in more improved mechanical property.

Thermal Load Simulation

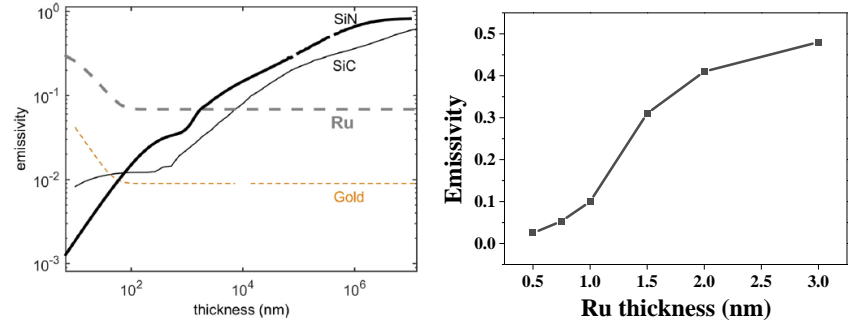
Emission is the only cooling mechanism of EUV pellicle (no conduction/ no convection)



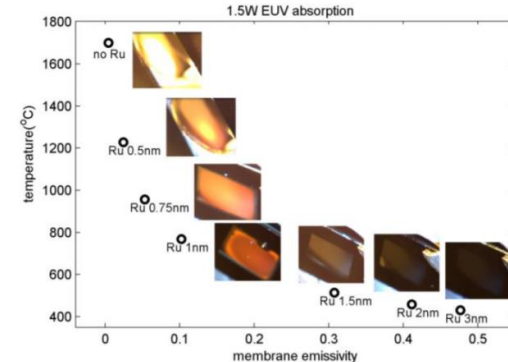
Material	Peak temperature [K]	Emissivity
pSi	541.71	0.5
SiC	505.15	0.75
Graphene	492.29	0.85
SiN _x	1678.5	0.0035

High emissivity material shows low peak temperature
Note: with bulk emissivity (not thin film emissivity)
with same thickness (not same transmittance)

Emissivity depends on the thickness !!

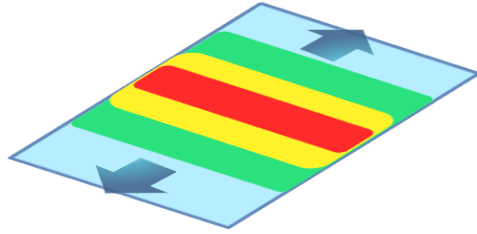


Thin metallic coating (~nm) enhances emission



Ref. P. J. van Zwol et al., J. Appl. Phys., 118(21), 211307 (2013).

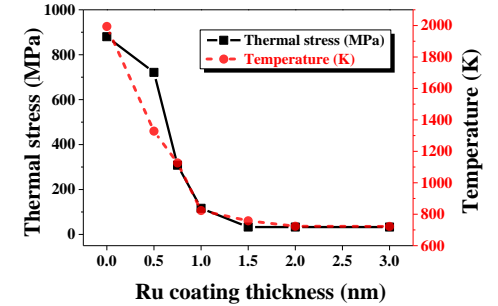
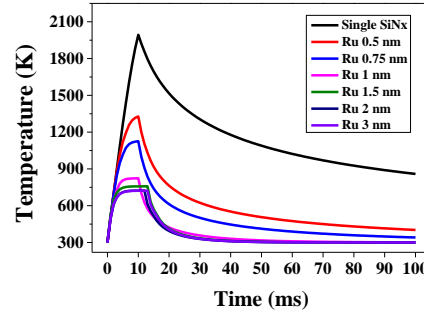
Thermal Stress



Single film thermal stress equation
(for edge clamped case)

$$\sigma = \frac{1}{2} \cdot E \cdot \alpha \cdot \Delta T$$

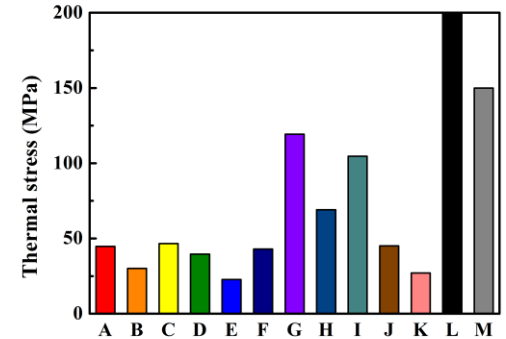
Ru coating enhances emission and decreases thermal stress



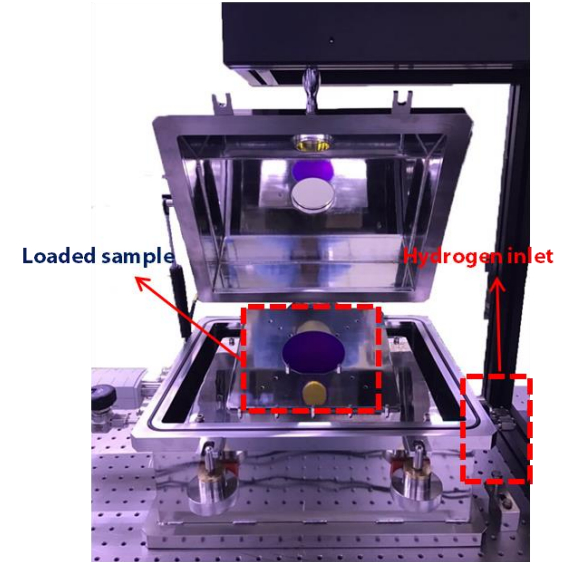
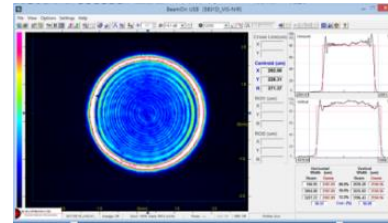
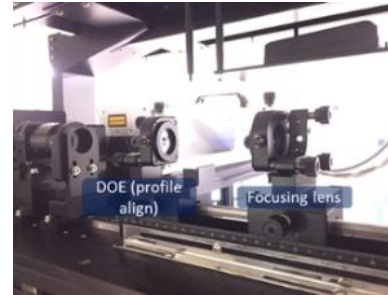
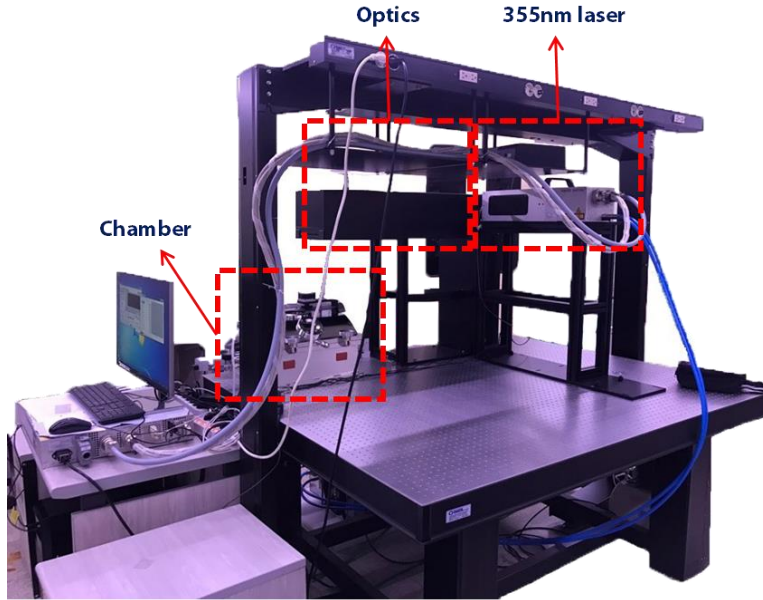
Emission layer candidates: B₄C as well as Ru

A	Ru	1 nm	B	B ₄ C	1 nm	C	B ₄ C	4 nm	D	Ru	1 nm	E	B ₄ C	1 nm	F	B ₄ C	4 nm
	SiNx	8 nm		SiNx	11 nm		SiNx	7 nm		Carbon	11 nm		Carbon	14 nm		Carbon	10 nm
	Ru	1 nm		B ₄ C	nm		B ₄ C	4 nm		Ru	1 nm		B ₄ C	1 nm		B ₄ C	4 nm
G	Ru	1 nm	H	B ₄ C	1 nm	I	B ₄ C	4 nm	J	Ru	1 nm	K	B ₄ C	1 nm	L	ASML pellicle	
	Carbon	12 nm		Carbon	14 nm		Carbon	8 nm		SiNx	5 nm		SiNx	7 nm		M	SAMSUNG pellicle
	SiNx	1 nm		SiNx	1 nm		SiNx	4 nm		Carbon	5 nm		Carbon	5 nm			
										Ru	1 nm		B ₄ C	1 nm			

* EUV transmittance 90 %



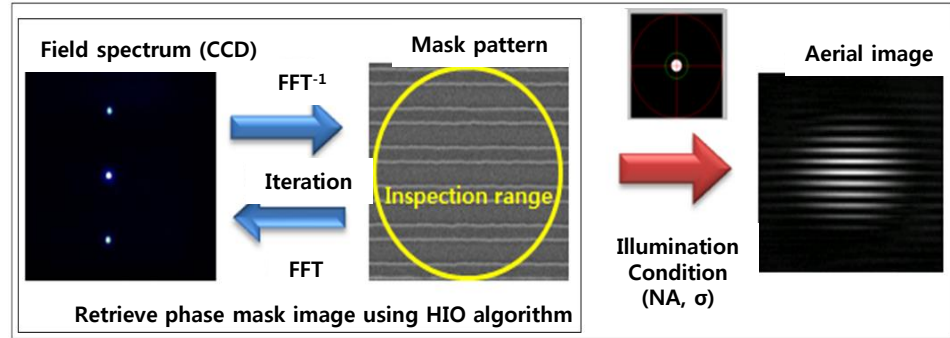
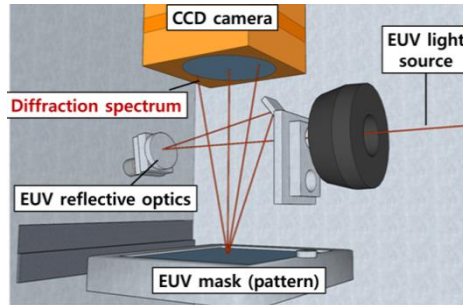
Thermal Load Test Platform



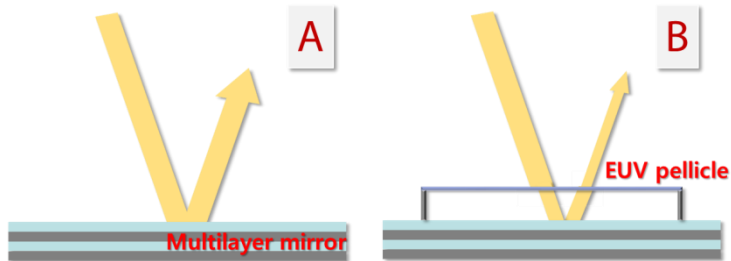
Thermal fatigue is an affliction occurring from sudden and repeated variations in the temperature of materials. The degree of damage is affected by the magnitude and frequency of the temperature swings. Damage comes in the form of cracking usually initiated on the surface and propagate through the material unless stopped until eventually causing structural failure.

Optical Characterization

CSM (Coherent Scattering Microscope)

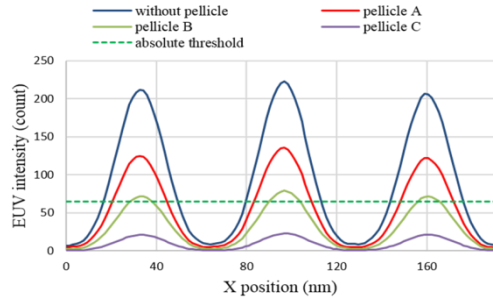


Evaluation set-up: Transmittance and Imaging Properties

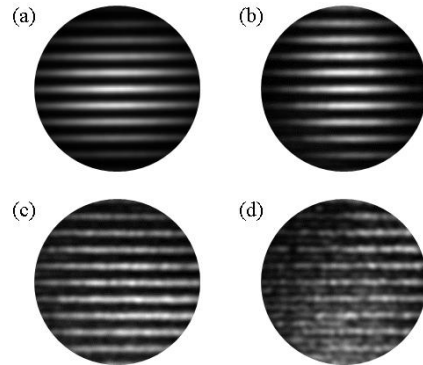


$$\text{one-pass EUV transmittance of pellicle} = \sqrt{\frac{B}{A}}$$

Optical Characterization

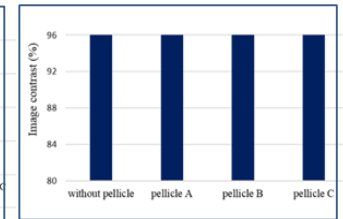
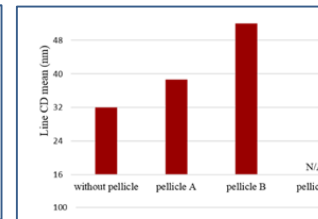
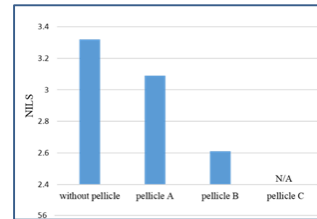


<Intensity profile of aerial image >



<Reconstructed aerial image >

Pellicle ^o	A ^o	B ^o	C ^o
Thickness (nm) ^o	43 ^o	93 ^o	175 ^o
Transmittance (%) ^o	78 ^o	60 ^o	30 ^o

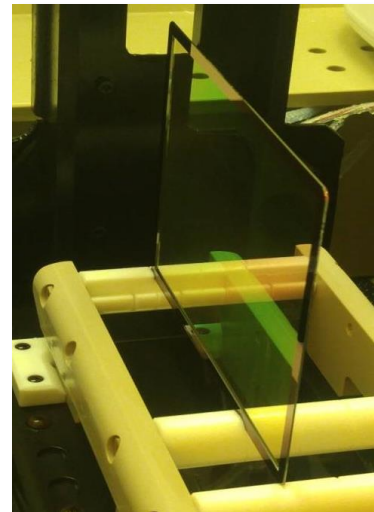
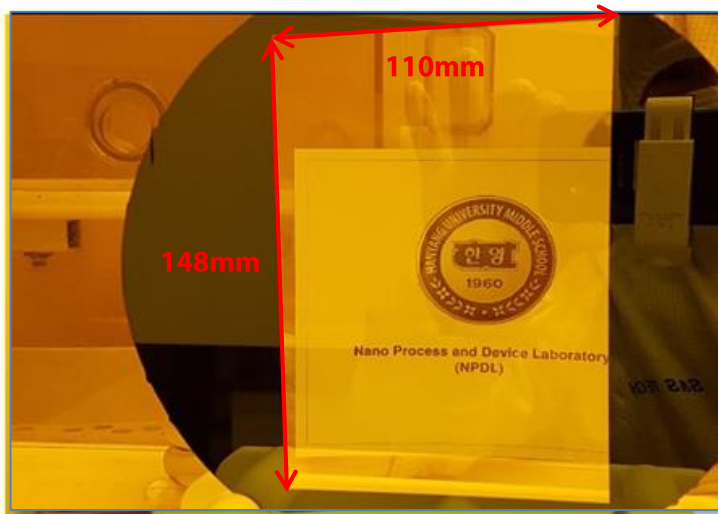


Line CD increased (+20.7%) and NILS decreased (-7.4%) with 78% transmittance pellicle by photon absorption

Although CD can be compensated by extending exposure time, high transmittance pellicle is desirable considering the throughput

Pellicle uniformity & local contamination control are more important for CDU

Full size SiN_x pellicle platform



Membrane material : SiN_x

Membrane thickness : ~40 nm

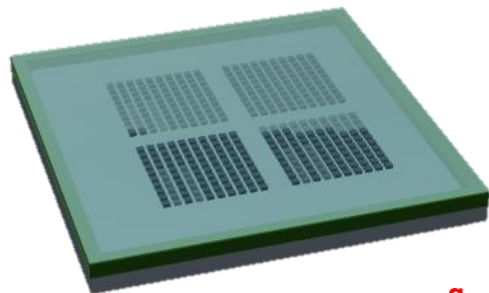
EUV transmittance : ~80%

Membrane size : 110 x 148 mm² (Full-size)

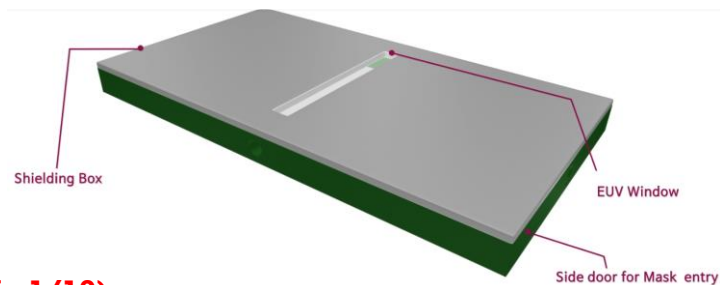
If pellicle solution is not available

Shielded Reticle Mini Environment (SRME)

EUV Pellicle



SRME



Small area membrane (x 1/19)
No risk of mechanical shock (No movement)
No repeated heating/ cooling (No fatigue)



Shielded Reticle Mini Environment(SRME)-EUV
Pellicle, EUV 펠리클

HYU kim
1개월 전 · 조회수 54회
Alternative method for EUV Pellicle!!

Thank you for your attention

